

COMPLETE LISTING OF CLAIMS

IN ASCENDING ORDER WITH STATUS INDICATOR

- 1.-26. (Cancelled)
27. (Original) An array of programmable conductor memories in an integrated circuit comprising pillars of stacked materials on a semiconductor substrate.
28. (Original) The array of Claim 27, wherein the regions between the pillars comprise insulating material.
29. (Original) The array of Claim 28, wherein the insulating material comprises silicon oxide.
30. (Original) The array of Claim 29, wherein the silicon oxide comprises tetraethylorthosilicate (TEOS).
31. (Original) The array of Claim 29, wherein there is a silicon nitride layer that conforms to the pillars and to the substrate below the silicon oxide.
32. (Original) The array of Claim 31, wherein the silicon nitride layer is between 5 nm and 50 nm thick.
- 33.-48. (Cancelled)